IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Patent application of

Makoto IWAI et al

Serial No.: (new - based on PCT/JP2005/006692)

Int'l Filing Date: March 30, 2005

For: GALLIUM NITRDIE SINGLE CRYSTAL GROWING

METHOD AND GALLIUM NITRIDE SINGLE CRYSTAL

PRELIMINARY AMENDMENT

Customer Window U.S. Patent & Trademark Office Randolph Building 401 Dulany Street Alexandria, VA 22314

Sir:

Prior to initial examination, please amend the above-identified application as follows: